

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|--|---|------------------|
| 1 | 162 | 430/311-313,394.ccls. and (interlac\$ or intertwin\$ or double adj expos\$) | USPAT; US-PGPUB; JPO | 2003/02/10 18:03 |
| 2 | 1 | 430/311-313,394.ccls. and (interlac\$ or intertwin\$ or double adj expos\$) | EPO; DERWENT; IBM_TDB | 2003/02/10 18:15 |
| 5 | 4 | (((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)).and 430/312.ccls. | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/02/10 18:21 |
| 6 | 2 | (((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) and 430/312.ccls. | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/02/10 18:23 |
| 7 | 3 | (((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) and 430/394.ccls. | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/02/10 18:24 |
| 8 | 3 | (((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) and 430/313.ccls. | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/02/10 18:25 |
| 10 | 331 | 430/312,394.cor. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/10 18:34 |
| 12 | 1717 | 430/312,394.ccls. not 430/312,394.cor. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/10 18:52 |

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|----|------|---|---|------------------|
| 13 | 3071 | (430/311-313,394.ccls. not 430/312,394.ccls. not 430/312,394.cor.) and pd>20021204 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/10 19:19 |
| 14 | 76 | (430/311-313,394.ccls. not 430/312,394.ccls. not 430/312,394.cor.) not @pd<=20021204 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/10 19:20 |
| - | 6 | ((5425848") or ("5817242") or ("6027595") or ("5512131") or ("5900160") or ("5925259")).PN. | USPAT; US-PGPUB; JPO | 2002/10/29 18:38 |
| - | 146 | 430/311-313,394.ccls. and (interlace\$ or intertwine\$ or double adj expos\$) | USPAT; US-PGPUB; JPO | 2002/10/21 16:13 |
| - | 1 | "5604059".PN. | USPAT | 2002/10/21 14:40 |
| - | 1 | 430/311-313,394.ccls. and (interlac\$ or intertwin\$ or double adj expos\$) | EPO; DERWENT; IBM_TDB | 2003/02/10 18:15 |
| - | 146 | 430/311-313,394.ccls. and (interlac\$ or intertwin\$ or double adj expos\$) | USPAT; US-PGPUB; JPO | 2003/02/10 18:16 |
| - | 1 | "6042998".PN. | USPAT | 2002/10/21 18:09 |
| - | 1 | "5989952".PN. | USPAT | 2002/10/21 18:13 |
| - | 1 | "5841143".PN. | USPAT | 2002/10/21 18:15 |
| - | 4951 | 430/311-313,394.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/02/10 18:17 |
| - | 1481 | (photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2002/11/21 13:23 |
| - | 698 | ((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2002/11/21 13:55 |
| - | 541 | ((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4)) and ((line\$2 or parallel) same expos\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2002/11/21 13:56 |
| - | 398 | ((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4)) and ((line\$2 or parallel) same expos\$3)) and develop\$4 | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2002/11/21 13:56 |
| - | 66 | ((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4)) and ((line\$2 or parallel) same expos\$3)) and develop\$4 and (dynamic adj random adj access or DRAM) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2002/11/21 13:57 |

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|--|-----|--|------------------------------------|------------------|
| | 769 | ((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2002/11/21 13:56 |
| | 602 | ((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2002/11/21 13:56 |
| | 438 | ((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3) and develop\$4 | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2002/11/21 13:57 |
| | 74 | ((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3) and develop\$4) and (dynamic adj random adj access or DRAM) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2002/11/22 11:52 |
| | 331 | ((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3) and develop\$4) and (dynamic adj random adj access or DRAM or memory) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2002/11/22 11:55 |
| | 62 | ((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2002/11/22 13:35 |
| | 4 | ((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) and 430/312.ccls. | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/02/10 18:19 |

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| | | 2 (((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) and 430/394.ccls. | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/02/10 18:22 |
| | | 3 (((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) and 430/313.ccls. | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/02/10 18:23 |
| | | 3 (((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) and 430/311.ccls. | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/02/10 18:24 |

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|--|------|---|---|------------------|
| | 57 | (((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) not ((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) and 430/312.ccls.) not ((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) and 430/394.ccls.) not ((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) and 430/313.ccls.) not ((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) and 430/311.ccls.) 430/311-313, 394.ccls. | USPAT; US-PGPUB; EPO; JPO; IBM TDB | 2003/02/10 18:26 |
| | 5004 | | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/12/04 10:24 |

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|--|------|--|---|------------------|
| | 1 | <p>(430/311-313,394.ccls. and (interlac\$ or intertwin\$ or double adj expos\$)) not ((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5)) not ((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/312.ccls.) not ((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/394.ccls.) not ((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/313.ccls.) not ((((((photoresist or resist or photopolymer\$7) and (etch or etched or etching or etchant) and ((doubl\$3 or plural\$4) same expos\$) same (perpendicular\$3 or cross\$3 or interlac\$3 or intertwin\$3 or row or column)) and semiconduct\$3 and (stor\$3 or capacit\$4 or memor\$5)) and ((line\$2 or parallel) same expos\$3)) and develop\$4) and (dynamic adj random adj access or DRAM or memory)) and ((round\$3 with corner) or (optical with proximity) or (line with short\$5))) and 430/311.ccls.))</p> <p>430/312,394.ccls.</p> | USPAT; US-PGPUB; EPO; JPO; IBM TDB | 2002/12/04 10:03 |
| | 2009 | | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/12/04 10:27 |

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| | 324 | 430/312,394.cor. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT | 2003/02/10 18:34 |
| | 13 | ("4591540" "5286584" "5308741" "5340700" "5424154" "5532090" "5563012" "5620816" "5702868" "5804339" "5807649" "5851707" "5863677").PN. | | 2002/12/04 12:36 |
| | 1685 | 430/312,394.cccls. not 430/312,394.cor. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; | 2003/02/10 18:51 |
| | 2995 | 430/311-313,394.cccls. not 430/312,394.cccls. not 430/312,394.cor. | US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; | 2003/02/10 19:12 |
| | 2 | (("5103274") or ("5120671")).PN. | US-PGPUB | 2002/12/07 14:02 |
| | 3 | ((("6184151") or ("5955244") or ("20010028422"))).PN. | USPAT; US-PGPUB | 2002/12/10 14:44 |